

## CLAIMS

1. A ceramic substrate, for a semiconductor  
producing/examining device, having a conductor formed inside  
5 thereof or on the surface thereof,  
wherein said ceramic substrate has been sintered such that  
a fractured section thereof exhibits intergranular fracture.
2. The ceramic substrate for a semiconductor  
10 producing/examining device according to claim 1,  
wherein an average diameter of ceramic grains of said  
fractured section is 0.5 to 10  $\mu\text{m}$ .
3. The ceramic substrate for a semiconductor  
15 producing/examining device according to claim 1,  
wherein an impurity element is locally distributed in  
boundaries of ceramic grains of said fractured section.
4. The ceramic substrate for a semiconductor  
20 producing/examining device according to claim 1,  
wherein thermal conductivity of said ceramic substrate  
is 100 W/m $\cdot$ K or more.
5. The ceramic substrate for a semiconductor  
25 producing/examining device according to claim 1,  
wherein said ceramic substrate is constituted such that:  
an impurity-existent area where an impurity element is  
locally distributed in triple points of crystal grains, and  
an impurity element-nonexistent area where an impurity  
30 is not locally distributed in the triple points of the crystal  
grains,  
coexist therein.